

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

5LN01S — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Ultrahigh-speed switching
- · 2.5V drive

Specifications

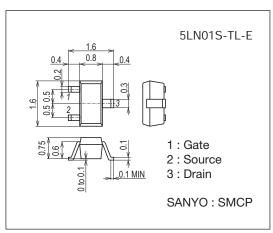
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		50	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		0.1	А
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	0.4	А
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity $< 200V^*$ ", so please take care when handling.

Package Dimensions

unit : mm (typ) 7027-004

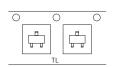


Product & Package Information

• Package : SMCP

• JEITA, JEDEC : SC-75, SOT-416 • Minimum Packing Quantity : 3,000 pcs./reel

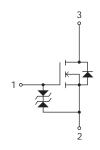
Packing Type: TL





Marking

Electrical Connection



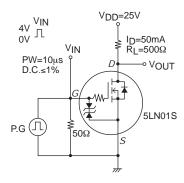
^{*} Machine Model

5LN01S

Electrical Characteristics at Ta=25°C

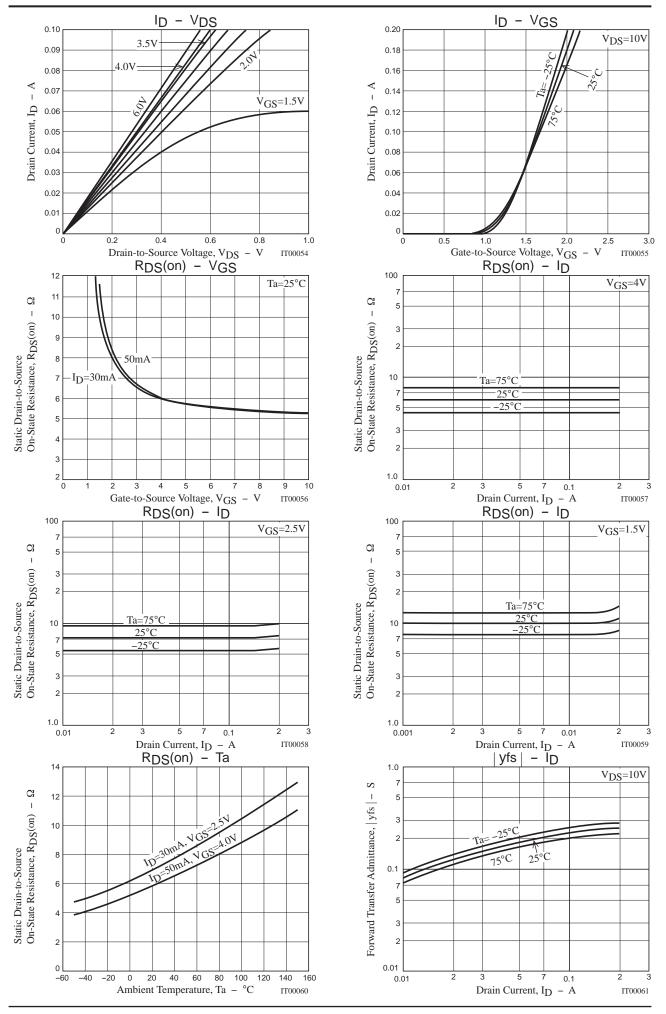
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	50			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =50V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =100μA	0.4		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =50mA	0.13	0.18		S	
	R _{DS} (on)1	I _D =50mA, V _{GS} =4V		6	7.8	Ω	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =30mA, V _{GS} =2.5V		7.1	9.9	Ω	
	R _{DS} (on)3	I _D =10mA, V _{GS} =1.5V		10	20	Ω	
Input Capacitance	Ciss			6.6		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		4.7		pF	
Reverse Transfer Capacitance	Crss			1.7		pF	
Turn-ON Delay Time	t _d (on)			18		ns	
Rise Time	t _r	Considered Total Circuit		42		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		190		ns	
Fall Time	tf			105		ns	
Total Gate Charge	Qg			1.57		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =100mA		0.20		nC	
Gate-to-Drain "Miller" Charge	Qgd			0.32		nC	
Diode Forward Voltage	V _{SD}	I _S =100mA, V _{GS} =0V		0.85	1.2	V	

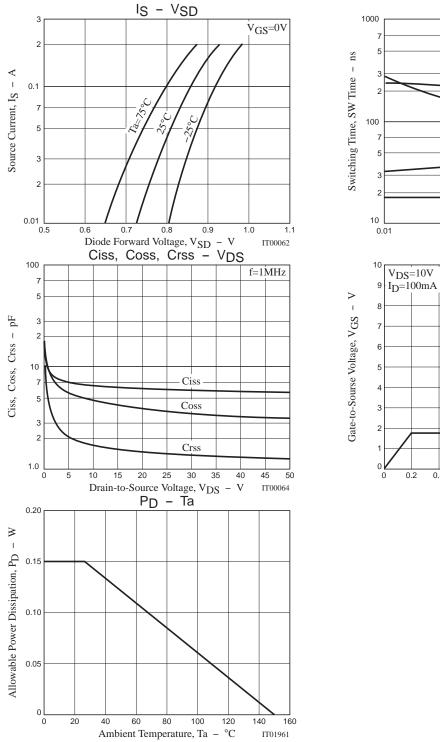
Switching Time Test Circuit

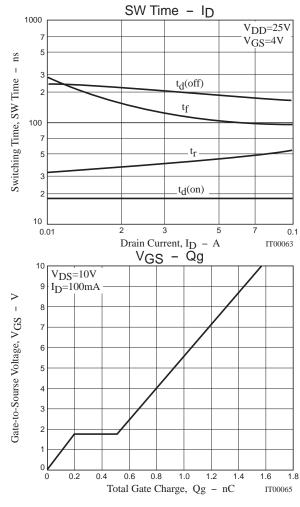


Ordering Information

Device	Package	Shipping	memo	
5LN01S-TL-E	LN01S-TL-E SMCP		Pb Free	





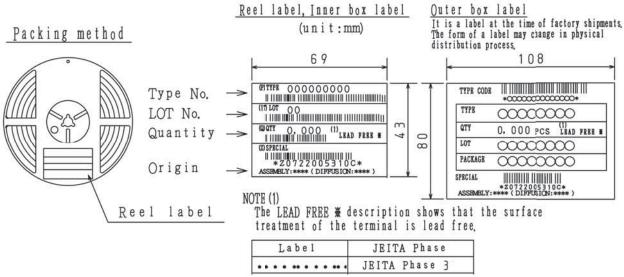


Embossed Taping Specification

5LN01S-TL-E

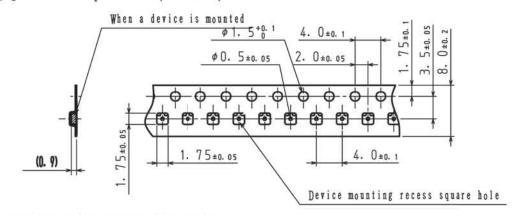
1. Packing Format

Package Name Carrier Tape		Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX $(A-7)$	
SMCP	SMCP	3, 000	15, 000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210	

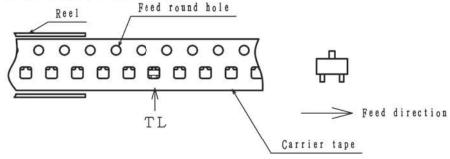


2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



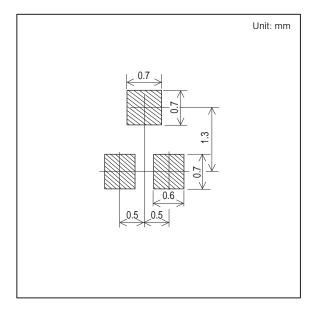
Those with one electrode terminal on the feed hole side TL

Outline Drawing

5LN01S-TL-E

| Mass (g) | Unit | 0.003 | ror reference | mm | 1.686.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4 | 0.886.1 | 0.4

Land Pattern Example



Note on usage: Since the 5LN01S is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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